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SiC

Silicon Carbide Diode

5th Generation thinQ!™

650V SiC Schottky Diode

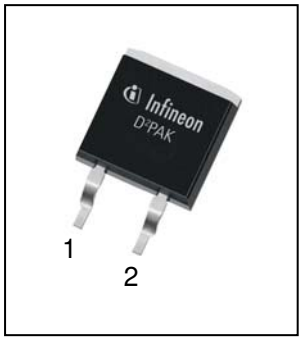
IDK02G65C5

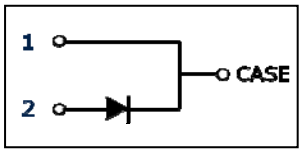
Final Data Sheet

Rev. 2.0, 2013-07-20

Power Management & Multimarket

5th Generation thinQ!™ SiC Schottky Diode IDK02G65C5





1 Description

ThinQ!™ Generation 5 represents Infineon leading edge technology for the SiC Schottky Barrier diodes. The Infineon proprietary diffusion soldering process, already introduced with G3 is now combined with a new, more compact design and thin-wafer technology. The result is a new family of products showing improved efficiency over all load conditions, resulting from both the improved thermal characteristics and a lower figure of merit (Qc x Vf).
The new thinQ!™ Generation 5 has been designed to complement our 650V CoolMOS™ families: this ensures meeting the most stringent application requirements in this voltage range.

Features

- Revolutionary semiconductor material - Silicon Carbide
- Benchmark switching behavior
- No reverse recovery/ No forward recovery
- Temperature independent switching behavior
- High surge current capability
- Pb-free lead plating; RoHS compliant
- Qualified according to JEDEC[1)] for target applications
- Breakdown voltage tested at 4.5 mA[2)]
- Optimized for high temperature operation

Benefits

- System efficiency improvement over Si diodes
- System cost / size savings due to reduced cooling requirements
- Enabling higher frequency / increased power density solutions
- Higher system reliability due to lower operating temperatures
- Reduced EMI

Applications

- Switch mode power supply
- Power factor correction
- Solar inverter
- Uninterruptible power supply

Table 1 Key Performance Parameters

Parameter	Value	Unit
V_{DC}	650	V
Q_C; V_R=400V	4	nC
E_C; V_R=400V	0.7	µJ
I_F @ T_C < 155°C	2	A

Table 2 Pin Definition

Pin 1	Pin 2	Pin 3
C	A	n.a.

Type / ordering Code	Package	Marking	Related links
IDK02G65C5	PG-TO263-2	D0265C5	www.infineon.com/sic

1) J-STD20 and JESD22

2) All devices tested under avalanche conditions for a time periode of 10ms

Table of Contents

2 Maximum ratings

Table 3 Maximum ratings

Parameter	Symbol	Values			Unit	Note/Test Condition
		Min.	Typ.	Max.		
Continuous forward current	I_F	–	–	2	A	T_C < 155°C, D=1
Surge non-repetitive forward current, sine halfwave	$I_{F,SM}$	–	–	23		T_C = 25°C, t_p=10 ms
		–	–	22		T_C = 150°C, t_p=10 ms
Non-repetitive peak forward current	$I_{F,max}$	–	–	138		T_C = 25°C, t_p=10 µs
i²t value	$\int i^2dt$	–	–	2.6	A²s	T_C = 25°C, t_p=10 ms
		–	–	2.5		T_C = 150°C, t_p=10 ms
Repetitive peak reverse voltage	V_{RRM}	–	–	650	V	T_j = 25°C
Diode dv/dt ruggedness	dv/dt	–	–	100	V/ns	V_R=0..480 V
Power dissipation	P_{tot}	–	–	36	W	T_C = 25°C
Operating and storage temperature	$T_j;T_{stg}$	-55	–	175	°C	

3 Thermal characteristics

Table 4 Thermal characteristics TO-263-2

Parameter	Symbol	Values			Unit	Note/Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction-case	R_{thJC}	–	2.6	4.2	K/W	
Thermal resistance, junction-ambient [1)]	R_{thJA}	–	–	62		SMD version, device on PCB, minimal footprint
			35			SMD version, device on PCB, 6cm² cooling area[1)]

1) Device on 40mm*40mm*1.5mm one layer epoxy PCB FR4 with 6cm² copper area (thickness 70µm) for drain connection, PCB is vertical without air stream cooling.

4 Electrical characteristics

Table 5 Static characteristics

Parameter	Symbol	Values			Unit	Note/Test Condition
		Min.	Typ.	Max.		
DC blocking voltage	V_{DC}	650	–	–	V	I_R= 0.33 mA, T_j=25°C
Diode forward voltage	V_F	–	1.5	1.8		I_F= 2 A, T_j=25°C
		–	1.8	2.2		I_F= 2 A, T_j=150°C
Reverse current	I_R	–	0.1	330	µA	V_R=650 V, T_j=25°C
		–	0.02	90		V_R=600 V, T_j=25°C
		–	0.4	1300		V_R=650 V, T_j=150°C

Table 6 AC characteristics

Parameter	Symbol	Values			Unit	Note/Test Condition
		Min.	Typ.	Max.		
Total capacitive charge	Q_c	–	4		nC	V_R=400 V, *di/dt*=200A/µs, $I_F \le I_{F,MAX}$, T_j=150°C.
Total Capacitance	C	–	70	–	pF	V_R=1 V, *f*=1 MHz
		–	9.1	–		V_R=300 V, *f*=1 MHz
		–	8.9	–		V_R=600 V, *f*=1 MHz

5 Electrical characteristics diagrams

Table 7

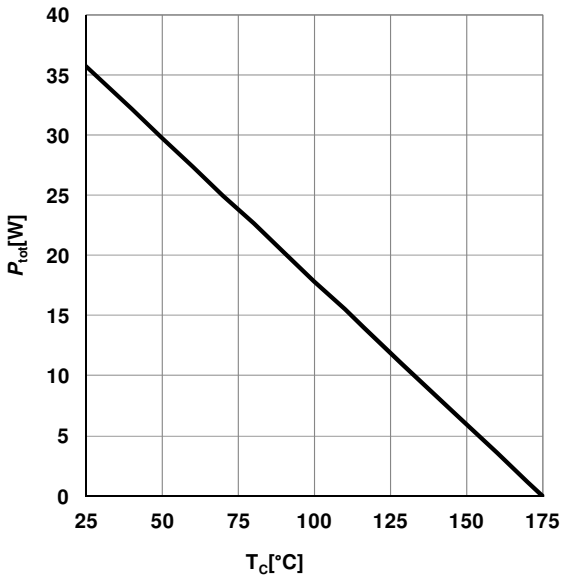
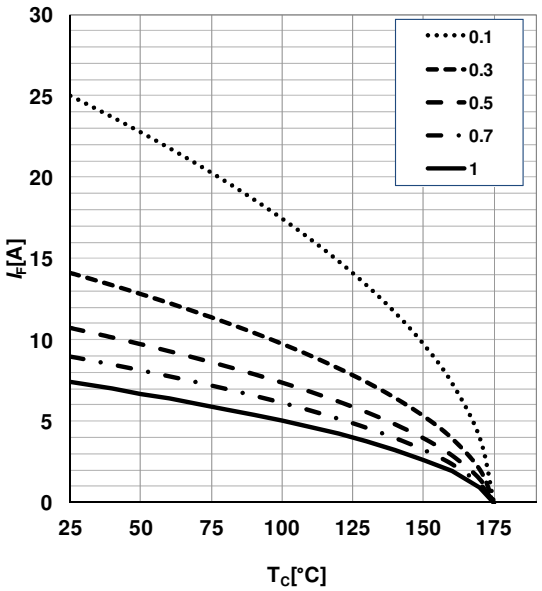
Power dissipation	Maximal diode forward current
	
$P_{tot}=f(T_C)$; $R_{thJC,max}$	$I_F=f(T_C)$; $R_{thJC,max}$; $T_j \leq 175°C$; parameter D=duty cycle

Table 8

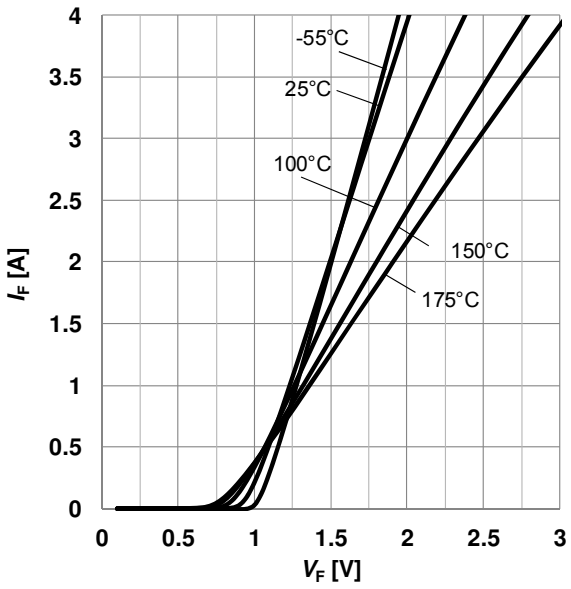
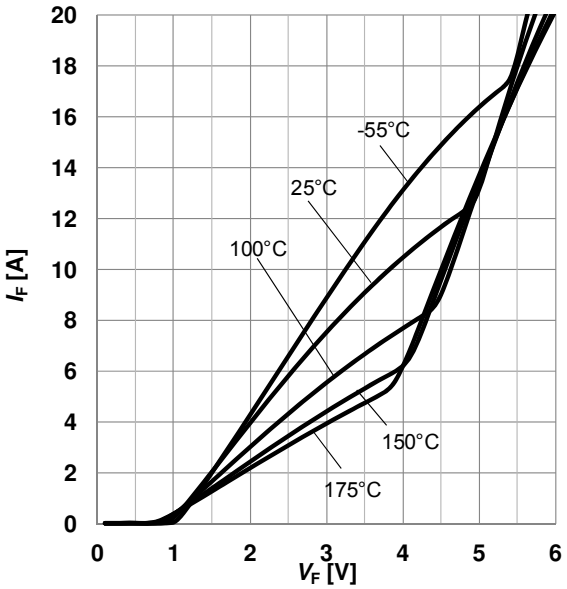
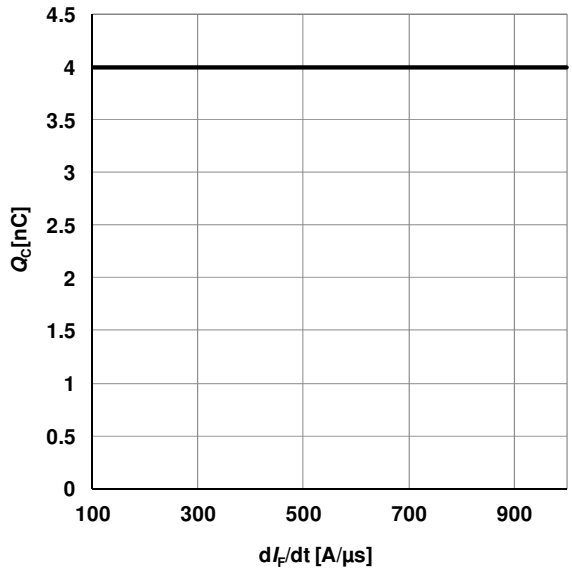
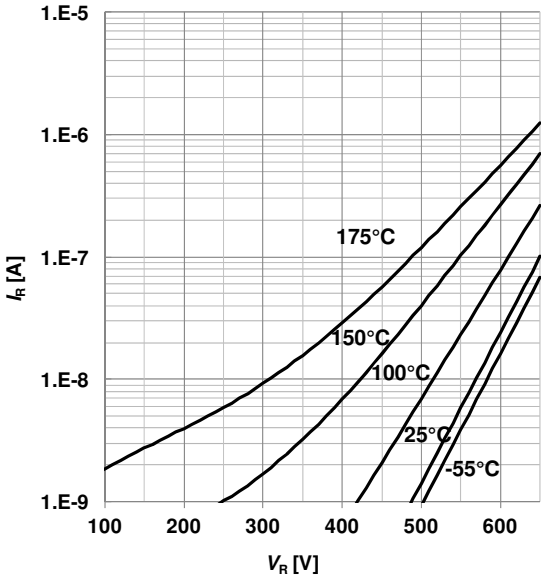
Typical forward characteristics	Typical forward characteristics in surge current
	
$I_F=f(V_F)$; t_p=200 µs; parameter: T_j	$I_F=f(V_F)$; t_p=200 µs; parameter: T_j

Table 9

Typ. capacitance charge vs. current slope[1)]	Typ. reverse current vs. reverse voltage
	
Q_C=f(dI_F/dt); T_j=150°C; V_R=400 V; $I_F \leq I_{F,max}$	I_R=f(V_R); parameter: T_j;

1) Only capacitive charge, guaranteed by design.

Table 10

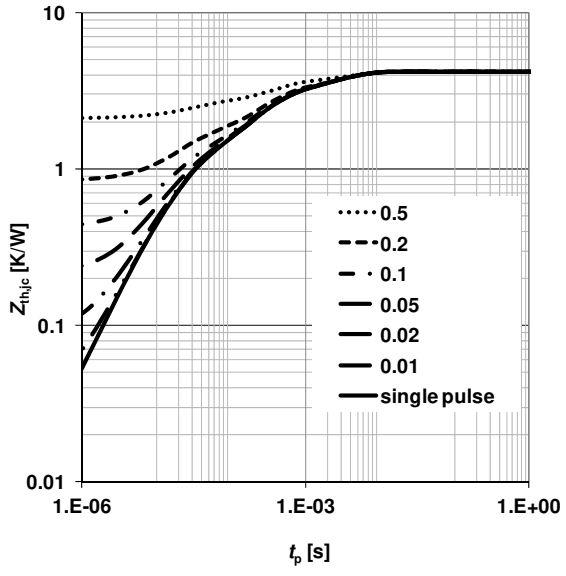
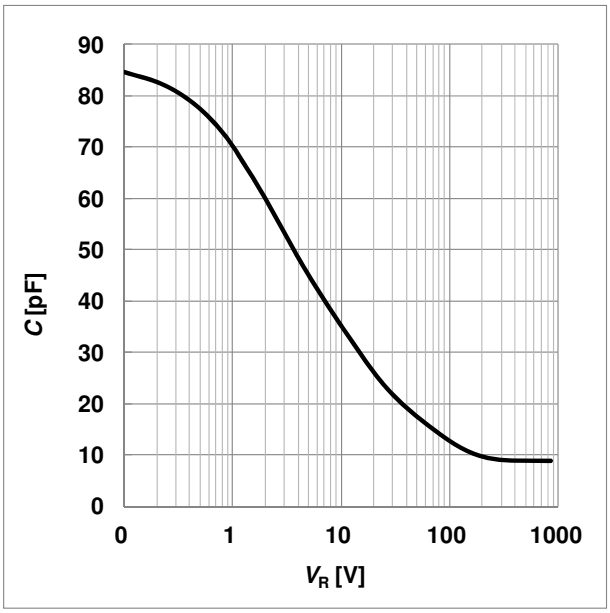
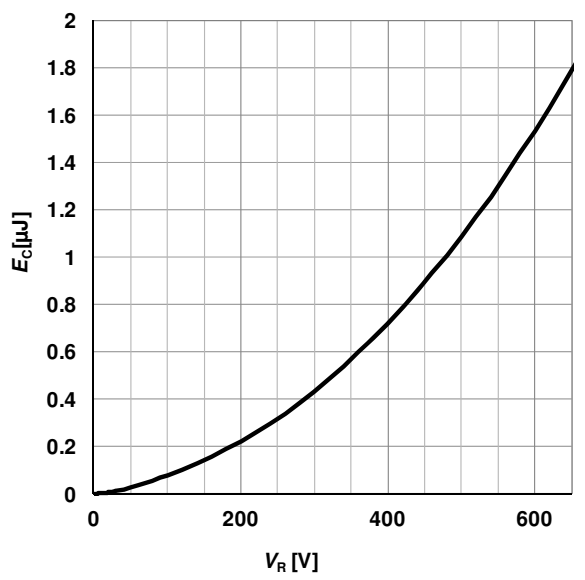
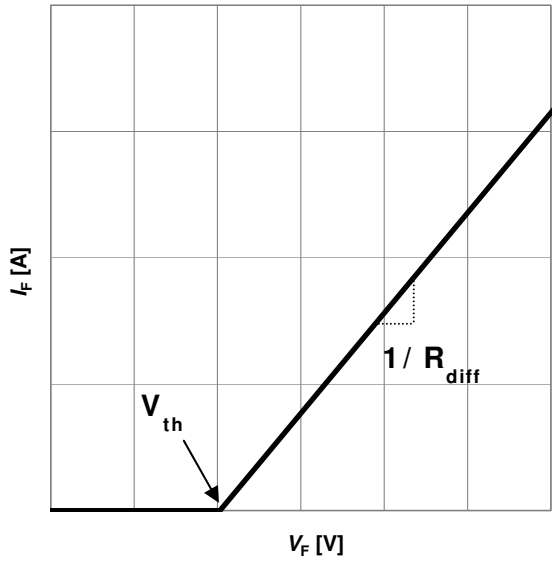
Max. transient thermal impedance	Typ. capacitance vs. reverse voltage
	
$Z_{th,jc}$=f(t_P); parameter: D=t_P/T;	C=f(V_R); T_j=25°C; f=1 MHz

Table 11

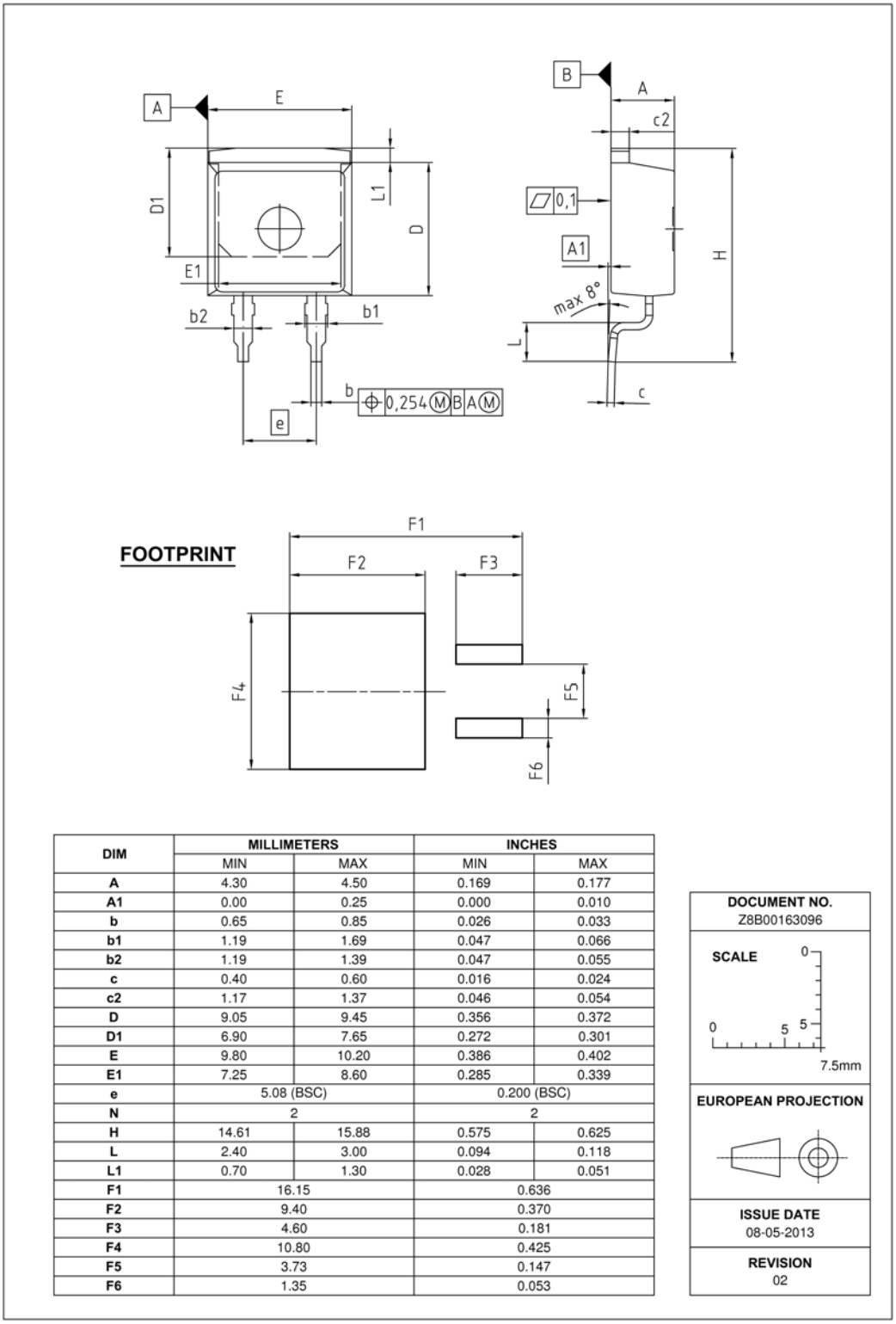
Typ. capacitance stored energy

E_C=f(V_R)

6 Simplified Forward Characteristics Model

Table 12

Equivalent forward current curve	Mathematical Equation
	$V_F = V_{TH} + R_{DIFF} \cdot I_F$ $V_{TH}(T_j) = -0.001 \cdot T_j + 1.04 \ [\mathrm{V}]$ $R_{DIFF}(T_j) = 6.42 \cdot 10^{-6} \cdot T_j^2 + 6.42 \cdot 10^{-4} \cdot T_j + 0.232 \ [\Omega]$
V_F=f(I_F)	T_j in °C; -55°C < T_j < 175°C; I_F < 4 A

7 Package outlines



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.30	4.50	0.169	0.177
A1	0.00	0.25	0.000	0.010
b	0.65	0.85	0.026	0.033
b1	1.19	1.69	0.047	0.066
b2	1.19	1.39	0.047	0.055
c	0.40	0.60	0.016	0.024
c2	1.17	1.37	0.046	0.054
D	9.05	9.45	0.356	0.372
D1	6.90	7.65	0.272	0.301
E	9.80	10.20	0.386	0.402
E1	7.25	8.60	0.285	0.339
e	5.08 (BSC)		0.200 (BSC)	
N	2		2	
H	14.61	15.88	0.575	0.625
L	2.40	3.00	0.094	0.118
L1	0.70	1.30	0.028	0.051
F1	16.15		0.636	
F2	9.40		0.370	
F3	4.60		0.181	
F4	10.80		0.425	
F5	3.73		0.147	
F6	1.35		0.053	

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SCALE 0 5 5 7.5mm

EUROPEAN PROJECTION

ISSUE DATE
08-05-2013

REVISION
02

Figure 1 Outlines TO-263-2, dimensions in mm/inches

8 Revision History

5th. Generation thinQ!™ SiC Schottky Diode

Revision History: 2013-07-20, Rev. 2.0

Previous Revision:

Revision	Subjects (major changes since last version)
2.0	Release of final data sheet

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